



2SK3018KWJ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30 V
I_D	200mA
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.5
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	3
Gate-Source ESD Rating Up to 2KV (HBM)	

General Description



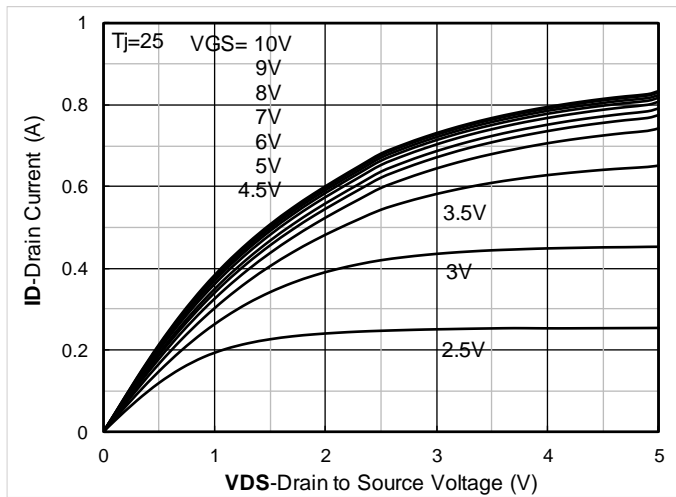
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=0$				



Typical Electrical and Thermal Characteristics Diagrams



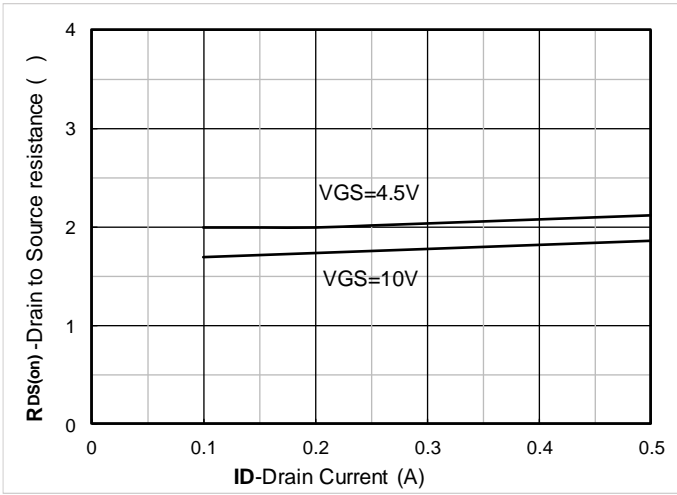


Figure 7. $R_{DS(on)}$ VS Drain Current

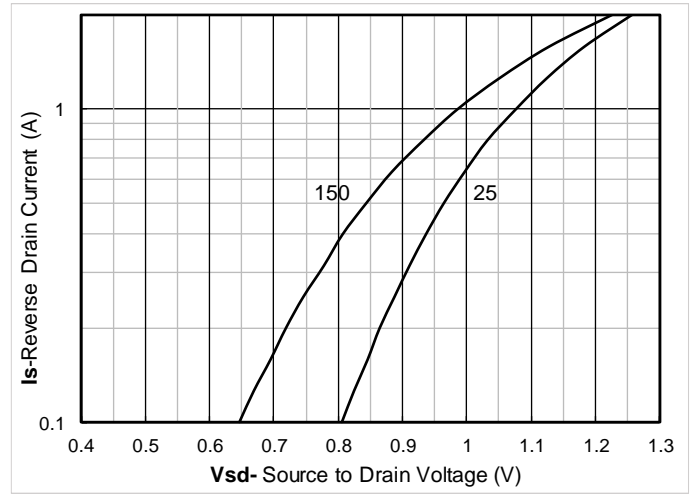


Figure 8. Forward characteristics of reverse diode

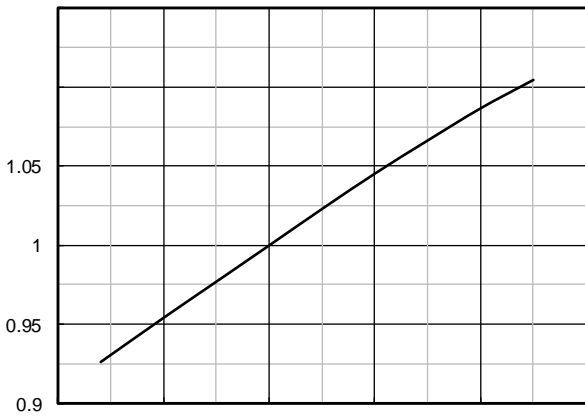


Figure 9. Normalized breakdown voltage

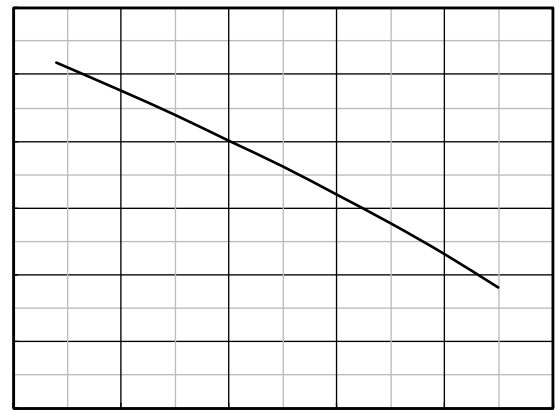


Figure 10. Normalized Threshold voltage

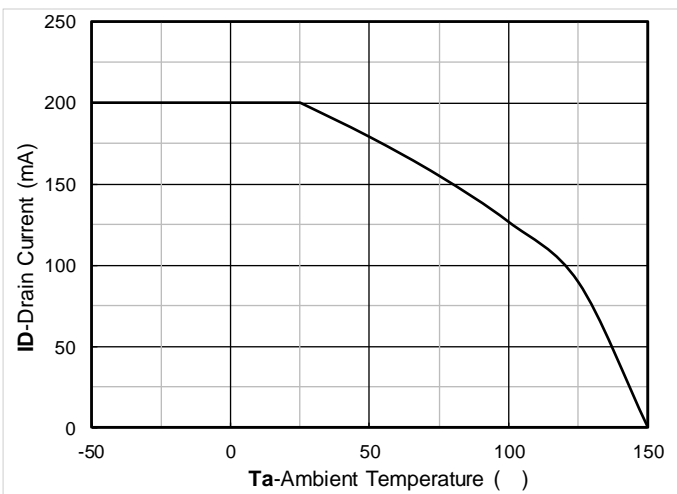


Figure 11. Current dissipation

Figure 12. Power dissipation

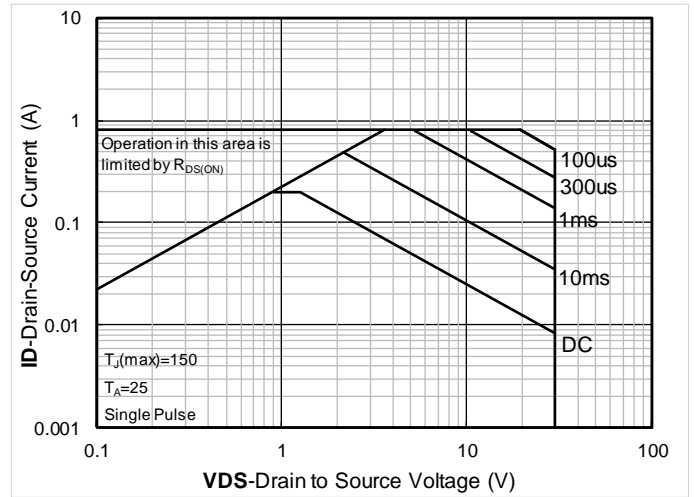


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

Test Circuits & Waveforms

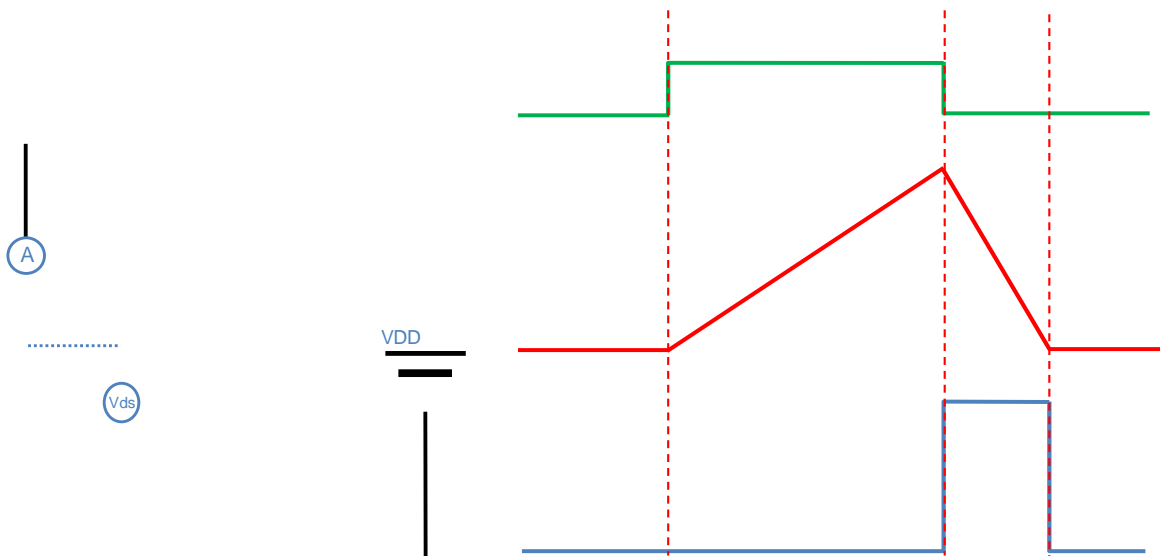


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

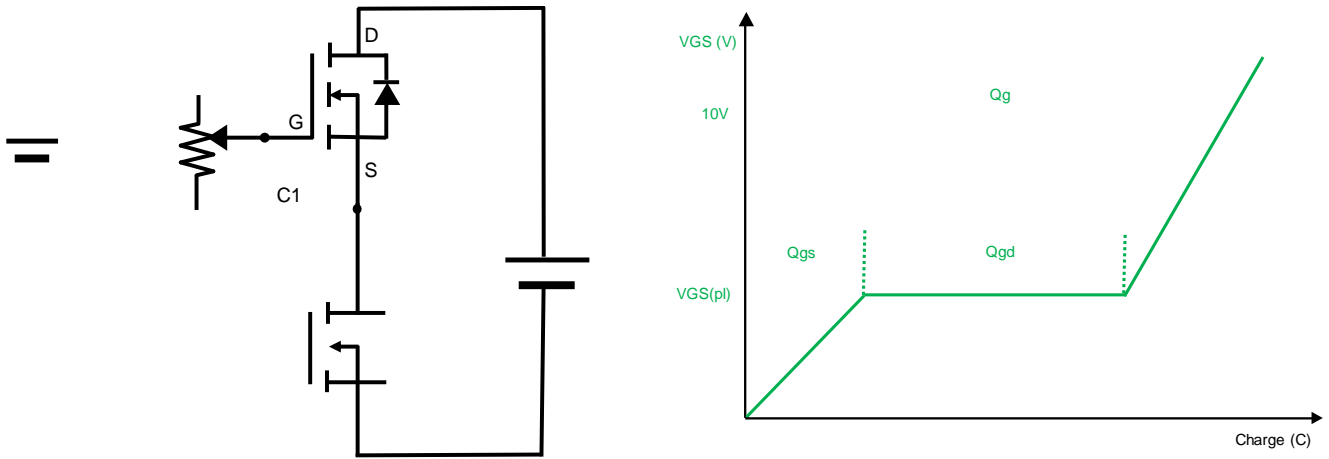


Figure B. Gate Charge Test Circuit & Waveform

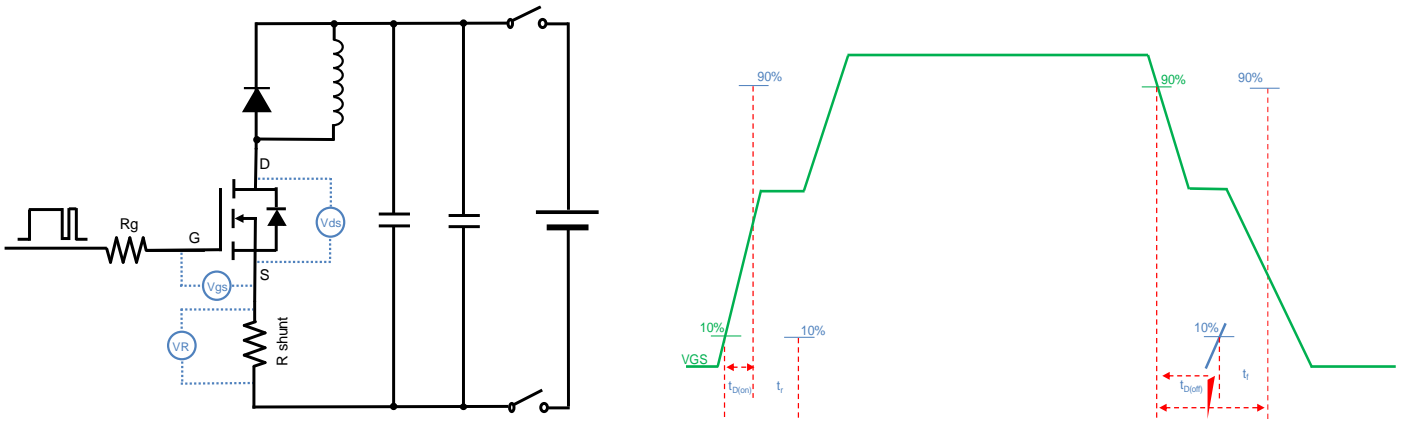


Figure C.



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SOT-323 Package information

DIMENSIONS		
SYMBOL	INCHES	
	MIN.	
A	0.035	
A1	0.000	
A2	0.035	
b	0.006	
c	0.004	
D		
E		
E1		

